



450V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _C = +25°C	
-450V	4.9Ω @ V _{GS} = -10V	-4.6A	

Description

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

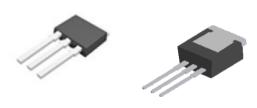
- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

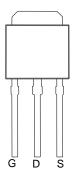
- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.33 grams (Approximate)



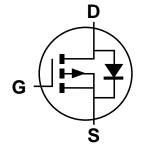


Bottom View

Top View



Top View



Internal Schematic

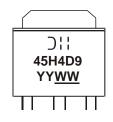
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP45H4D9HJ3	TO251 (Type TH)	75 Pieces / Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ I = Manufacturer's Marking
45H4D9 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)

DMP45H4D9HJ3 Document number: DS39244 Rev. 3 - 2



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-450	V		
Gate-Source Voltage			V _{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _C = +25°C T _C = +100°C	lσ	-4.6 -3.0	А
Maximum Body Diode Forward Current (Note 5)	ls	-3.0	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			IDM	-22.4	Α
Avalanche Current, L = 60mH (Note 7)			las	-2.5	Α
Avalanche Energy, L = 60mH (Note 7)			Eas	187	mJ
Peak Diode Recovery dv/dt (V _{DD} = -400V, I _D = -2.0A)			dv/dt	50	V/ns

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_C = +25^{\circ}C$	D-	104	W	
Total Power Dissipation (Note 5)	Tc = +100°C	PD	41		
Thermal Resistance, Junction to Ambient (Note 6)	RθJA	40	°C/W		
Thermal Resistance, Junction to Case (Note 5)	R _θ JC	1.2			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BVDSS	-450		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -450V, V_{GS} = 0V$		
Gate-Source Leakage	Igss			±100	nA	$V_{GS} = \pm 30V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	-3.0	-4.0	-5.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$		
Static Drain-Source On-Resistance	RDS(ON)		3.1	4.9	Ω	$V_{GS} = -10V, I_{D} = -1.05A$		
Diode Forward Voltage	V_{SD}			-1.3	V	$V_{GS} = 0V$, $I_{S} = -2.1A$		
DYNAMIC CHARACTERISTICS (Note 7)								
Input Capacitance	Ciss		547	_		V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz		
Output Capacitance	Coss	_	74	_	pF			
Reverse Transfer Capacitance	Crss	_	3.1	_				
Total Gate Charge (V _{GS} = -10V)	Qg	_	13.7	_				
Gate-Source Charge	Qgs	_	3.4	_	nC	$V_{DS} = -360V$, $I_{D} = -2.7A$, $V_{GS} = -10V$		
Gate-Drain Charge	Q_{gd}	_	6.0	_				
Turn-On Delay Time	tD(ON)	_	19	_		$V_{DD} = -225V$, $R_G = 3.0\Omega$, $I_D = -2.7A$		
Turn-On Rise Time	t _R	_	40	_				
Turn-Off Delay Time	tD(OFF)	_	32	_	ns			
Turn-Off Fall Time	tF		31	_				
Body Diode Reverse Recovery Time	t _{RR}	_	164	_	ns	V _G S = 0V, V _{DD} = -200V, I _S = -2.7A,		
Body Diode Reverse Recovery Charge	Q _{RR}		1.3	_	nC	dl/dt = 100A/µs		

Notes:

- 5. Device mounted on infinite heatsink.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 7. Guaranteed by design. Not subject to production testing.
 8. Short duration pulse test used to minimize self-heating effect.



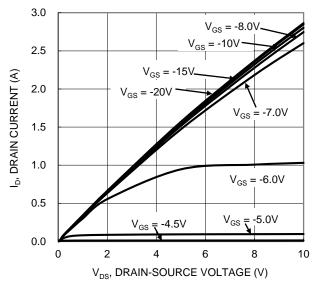


Figure 1. Typical Output Characteristic

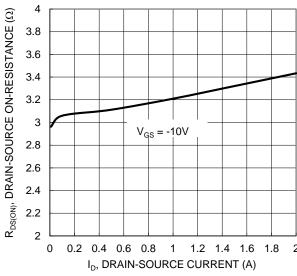


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

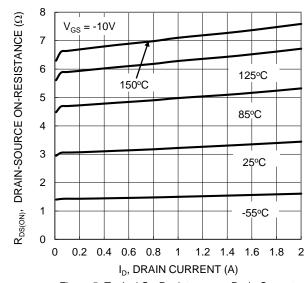


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

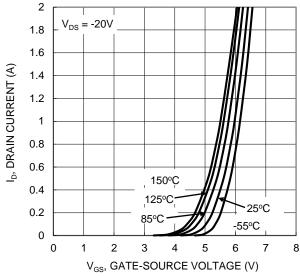


Figure 2. Typical Transfer Characteristic

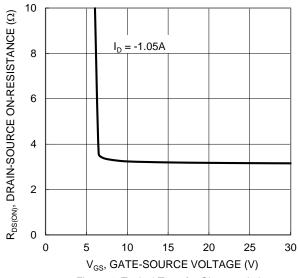


Figure 4. Typical Transfer Characteristic

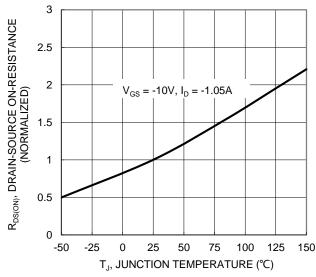


Figure 6. On-Resistance Variation with Temperature



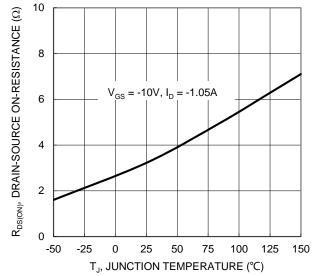
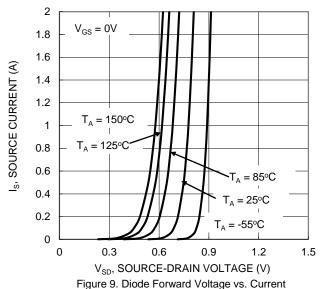


Figure 7. On-Resistance Variation with Temperature



10 8 6 $V_{DS} = -360V, I_{D} = -2.7A$ $V_{GS}(V)$ 4 2 0 0 2 8 10 12 14 Q_g (nC) Figure 11. Gate Charge

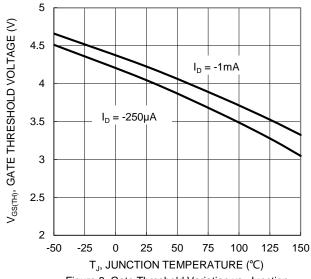


Figure 8. Gate Threshold Variation vs. Junction Temperature

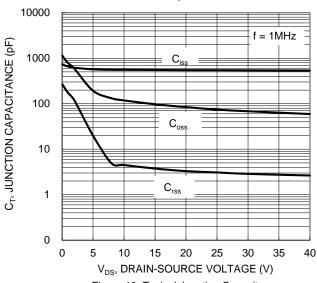


Figure 10. Typical Junction Capacitance

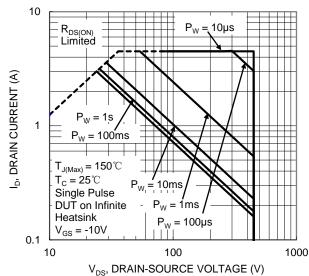


Figure 12. SOA, Safe Operation Area



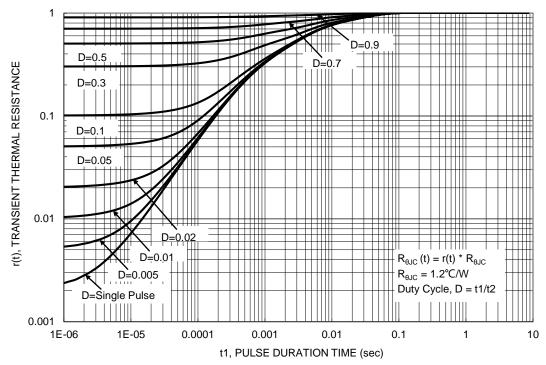


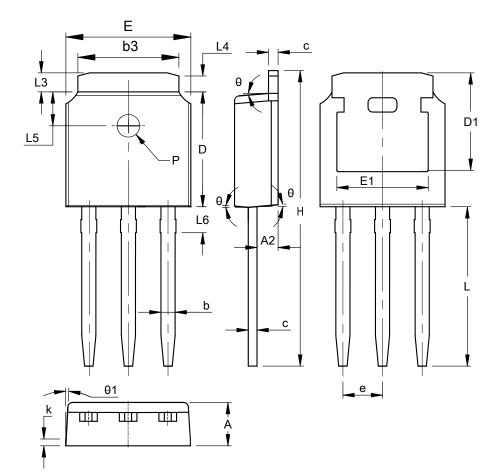
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO251 (Type TH)



TO251 (Type TH)						
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b3	5.20	5.50	5.33			
С	0.43	0.63	0.53			
D	5.98	6.22	6.10			
D1	5	.30 RE	F			
е	2.	286 BS	Ö			
Е	6.40	6.80	6.60			
E1	4.63	5.03	4.83			
Н	16.22	16.82	16.52			
k	0).40REI	=			
L	9.15	9.65	9.40			
L3	0.88	1.28	1.02			
L4	0.75 REF					
L5	1.65	1.95	1.80			
L6	0.85	1.25	1.05			
PØ	1.20					
θ	5°	9°	7°			
θ1	5°	9°	7°			
All Dimensions in mm						



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